2SC1515(K)

Silicon NPN Triple Diffused

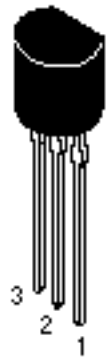
HITACHI

Application

High voltage switching

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

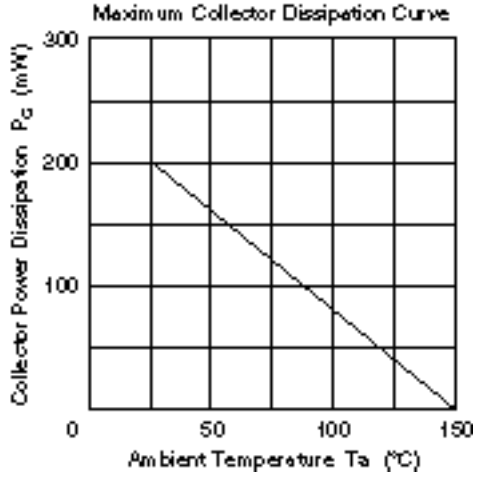
Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	200	V
Collector to emitter voltage	V_{CES}	200	V
	V_{CEO}	150	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

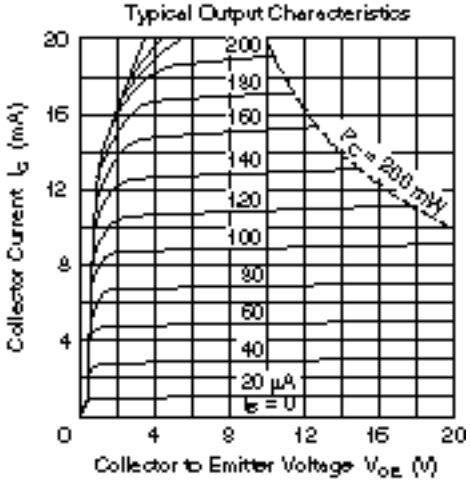
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CES}$	200	—	—	V	I_C = 10 µA, R_{BE} = 0
	$V_{(BR)CEO}$	150	—	—	V	I_C = 1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	I_E = 10 µA, I_C = 0
Collector cutoff current	I_{CBO}	—	—	0.1	µA	V_{CB} = 20 V, I_E = 0
DC current transfer ratio	h_{FE}	30	—	300		V_{CE} = 6 V, I_C = 10 mA
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.0	V	I_C = 10 mA, I_B = 1 mA
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	I_C = 10 mA, I_B = 1 mA
Gain bandwidth product	f_T	60	—	—	MHz	V_{CE} = 6 V, I_C = 10 mA
Collector output capacitance	Cob	—	—	10	pF	V_{CB} = 6 V, I_E = 0, f = 1 MHz

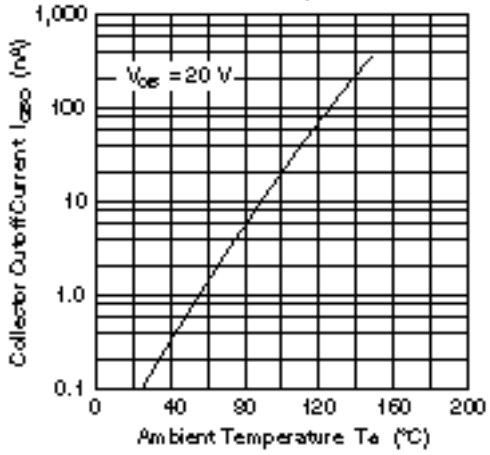
Maximum Collector Dissipation Curve



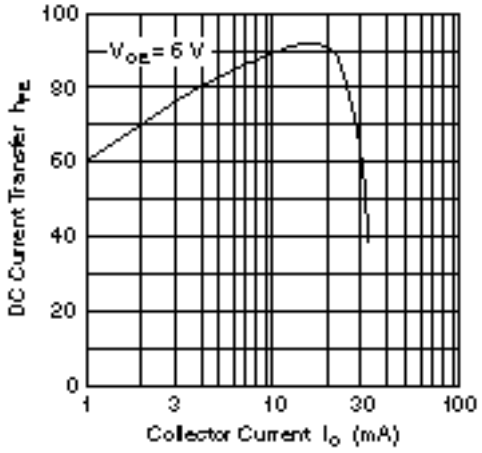
Typical Output Characteristics



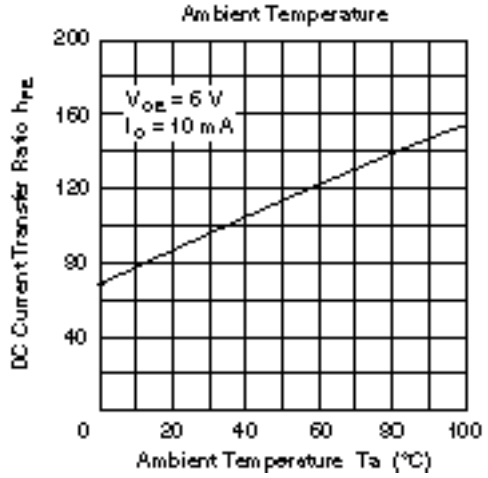
Collector Cutoff Current vs. Ambient Temperature



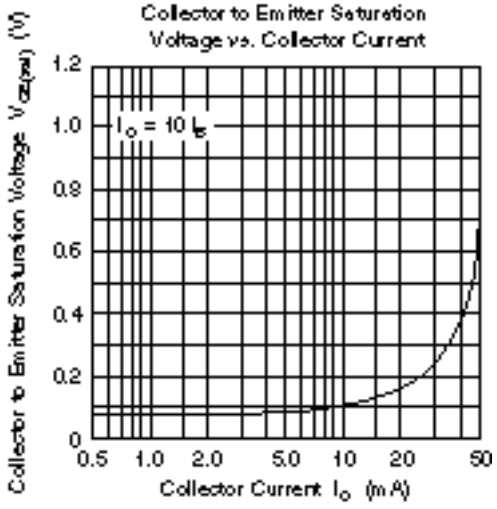
DC Current Transfer Ratio vs. Collector Current



DC Current Transfer Ratio vs. Ambient Temperature



Collector to Emitter Saturation Voltage vs. Collector Current



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